

AMENDMENTS TO CLAIMS

Listing Of Claims

Claims 1-33 (Canceled)

34. (Currently amended) A method for fabricating an interconnect for a ~~semiconductor component having engaging~~ a bumped contact on a semiconductor component comprising:
providing a substrate;
~~having a surface and an opposing surface;~~
forming a plurality of leads on the substrate surface configured to electrically engage and support the bumped contact;
~~and a connecting segment on the surface configured to electrically connect the leads to one another;~~
forming a recess in the surface substrate such that the leads cantilever over the recess and are configured for movement within the recess during electrical engagement of the bumped contact; and
forming an outer layer on each lead configured to provide a non-bonding surface for the bumped contact.
~~forming a conductive via in the substrate in electrical communication with the connecting segment; and~~
~~forming a contact on the opposing surface in electrical communication with the conductive via.~~

35. (Currently amended) The method of claim 34 wherein the outer layer comprises a material selected from the group consisting of Ti, TiSi₂, Al and a conductive polymer.

~~forming the conductive via step comprises forming an opening through the connecting segment and the substrate and forming a conductive material in the opening.~~

Claims 36-37 (Withdrawn)

38. (Currently amended) The method of claim 34 further comprising forming at least one blade ~~s on the~~ leads on each lead configured to penetrate the bumped contact.

39. (Currently amended) A method for fabricating an interconnect for a ~~semiconductor component having~~ engaging a bumped contact on a semiconductor component comprising:

providing a substrate;
~~having a surface and an opposing surface;~~
forming a metal layer on the substrate;
forming a plurality of blades in the metal layer
configured to penetrate the bumped contact;
forming an outer layer on the metal layer configured
to provide a non-bonding surface for the bumped contact;

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forming a plurality of leads ~~on the surface in the~~ metal layer configured to electrically engage and support the bumped contact, each lead including at least one blade;
and

~~and a connecting segment on the surface configured to electrically connect the leads to one another;~~

forming a recess in the ~~surface~~ substrate such that the leads are cantilevered over the recess and are configured to move within the recess during electrical engagement of the bumped contact.

forming an opening through the substrate and the connecting segment;

forming a conductive material in the opening; and
forming a contact on the opposing surface in
electrical communication with the conductive material.

40. (Currently amended) The method of claim 39 wherein the outer layer comprises a conductive polymer.

~~forming the opening step comprises laser machining.~~

41. (Currently amended) The method of claim 39 wherein the outer layer comprises a material selected from the group consisting of a carbon film and a metal filled silicone.

~~recess is generally square having four sides and the leads extend generally orthogonally to the four sides.~~

Claim 42 (Withdrawn)

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43. (Currently amended) The method of claim 39 further comprising forming a connecting segment on the substrate electrically connecting the leads, a conductive via in the substrate in electrical communication with the connecting segment and a contact on the substrate in electrical communication with the conductive via.

~~plurality of blades on the leads configured to penetrate the bumped contact.~~

Claims 44-48 (Withdrawn)

49. (Currently amended) A method for fabricating an interconnect for ~~a semiconductor component having a~~ engaging bumped contacts on a semiconductor component comprising:

providing a substrate having a surface and an opposing surface;

forming a plurality of interconnect contacts on the substrate configured to electrically engage the bumped contacts, each interconnect contact comprising a recess in the surface and a plurality of leads cantilevered over the recess configured to support a bumped contact for movement in the recess; and

forming an outer layer on each lead configured to provide non-bonding surfaces for the bumped contacts.

~~forming a plurality of conductive vias in the substrate in electrical communication with the interconnect contacts; and~~

~~forming a plurality of contacts on the opposing surface having a different pitch than that of the interconnect contacts.~~

50. (Currently amended) The method of claim 49 wherein the outer layer comprises a conductive polymer.
~~contacts comprise pads.~~

51. (Currently amended) The method of claim 49 further comprising forming ~~a plurality of~~ at least one blade ~~on the~~ each lead ~~is~~ configured to penetrate ~~the~~ a bumped contact.

52-58. (Withdrawn)